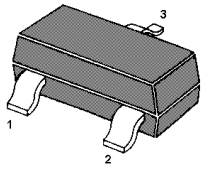
MMBTSA1576

PNP Silicon Epitaxial Planar Transistor

The transistor is subdivided into three groups Q, R and S according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1.BASE 2.EMITTER 3.COLLECTOR

SOT-23 Plastic Package

Feature

- Excellent h_{FE} linearity

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	150	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{Stg}	-55 to +150	°C

Characteristics at T_{amb}=25 °C

		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain						
at $-V_{CE}$=6V, $-I_C$=1mA	Q	h_{FE}	120	-	270	-
	R	h_{FE}	180	-	390	-
	S	h_{FE}	270	-	560	-
Collector Cutoff Current						
at $-V_{CB}$=60V		$-I_{CBO}$	-	-	0.1	µA
Emitter Cutoff Current						
at $-V_{EB}$=6V		$-I_{EBO}$	-	-	0.1	µA
Collector Saturation Voltage						
at $-I_C$=50mA, $-I_B$=5mA		$-V_{CE(sat)}$	-	-	0.5	V
Collector Base Breakdown Voltage						
at $-I_C$=50µA		$-V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage						
at $-I_C$=1mA		$-V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage						
at $-I_E$=50µA		$-V_{(BR)EBO}$	6	-	-	V
Transition Frequency						
at $-V_{CE}$=12V, $-I_E$=2mA, f=30MHz		f_T	-	140	-	MHz
Output Capacitance						
at $-V_{CB}$=12V, f=1MHz		Cob	-	4.0	5	pF